Comment on the possibility of Inverse Crystallization within van Hemmen's Classical Spin-Glass model

Eduardo Cuervo-Reyes¹

¹Laboratory of Inorganic Chemistry, Solid State, ETH-Zürich 8093 Switzerland (Dated: April 22, 2019)

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In reference[1], van Hemmen (vH) introduced a classical spin model with frustration, which is analytically solvable and reproduces many experimental features of a spin glass (SG) quite well[1]. It consists of N Ising-spins interacting via a long-range random coupling of the form $J_{ij} = J_0/N - (J/N)(\xi_i \eta_j + \xi_j \eta_i); \xi_i \text{ and } \eta_j \text{ are identi-}$ cally distributed random variables with zero mean and finite variance. J_0 is a net direct exchange, and J represents the strength of the strongly-oscillating and longranged Ruderman-Kittel-Kasuya-Yosida (RKKY) interaction. vH phase diagram (Fig.1) is universal[2, 3]; i.e., robust against variations of the distribution of ξ_i and η_i . The ferromagnetic state (FE), whenever it exists $(J_0/J > x_c = 2/\pi)$, is the low temperature phase; vH considered this is a limitation of his model. Apparently, it cannot account for phenomena such as inverse freezing, where an ordered phase appears at higher temperatures than a less-ordered one. This comment is intended to show that the vH model, in its original classical version, can also account for transitions from a SG phase to a higher-temperature FE state.

The so far ignored fact is the temperature dependence of J. For T > 0, the RKKY interaction becomes exponentially damped. The envelope function has the asymptotic form $I(T) = I(0)e^{-\pi T k_F r/T_F}$, for $T < T_F$, irrespective of the dimensionality[4]. T_F and k_F are the Fermitemperature and wave-vector, and r is the generic dis-

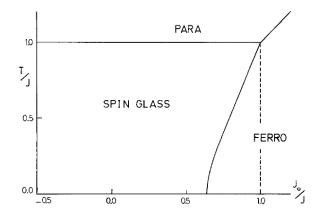


FIG. 1: Phase diagram of van Hemmen's classical spin model, at zero external field, with Gaussian-distributed exchange constants; taken from reference[2].

tance between two interacting magnetic centers. As J

is representative of the long-range RKKY coupling, this can be roughly estimated taking the value of the envelope function at $k_F r = \pi$. Hence, $J(T) \sim J(0)e^{-\gamma T}$, with $\gamma = \pi^2/T_F$ and J(0) = J(T = 0). For a given system, the corresponding $x = J_0/J$ will increase as one goes up in temperature. In other words, a system is represented by fixed $J_0/J(0)$ and γ ; heating/cooling a sample does not correspond to a vertical line in Fig.(1). A FE phase may appear upon heating a glass state if $\gamma J(0) \geq x_c^{-1} \ln (1/x_c)$; or in terms of T_F ,

$$J(0)/T_F \ge \pi^{-2} x_c^{-1} \ln\left(1/x_c\right). \tag{1}$$

To check whether this is a reasonable constraint, let use the effective mass approximation. The damping coefficient is rewritten as $\gamma = 4\pi^2 m^* k_B (3n_e/\pi)^{-2/3}/\hbar^2$, in terms of the effective mass m^* and concentration n_e of conduction electrons. k_B and \hbar are the the Boltzmannand Plank-constant. Substituting the respective values, we obtain

$$m_{\rm rel}^* n_e^{-2/3} J(0) \ge 10^{-17} \,{\rm K} \,{\rm m}^2$$
 (2)

where $m_{\rm rel}^*$ is the effective mass relative to the free electron mass. For a good metal $(n_e \sim 10^{28} {\rm m}^{-3})$, Eq.(2) gives $m_{\rm rel}^* J(0) \geq 50$ K; and for a bad metal or a doped semiconductor $(n_e \sim 10^{22} {\rm m}^{-3})$, $m_{\rm rel}^* J(0) \geq 0.005$ K. This is quite reasonable; therefore, vH model may reproduce the inverse crystallization of actual systems. Lastly, it is worth noting that the exponential decay of J can be also used above the tricritical point $(T/J = 1; J_0/J = 1)$, as long as the latter remains below the Fermi temperature. This will hold if $J(0)/T_F < e^{\pi^2}$, which is satisfied in most reasonable cases. Similarly, taking into account the temperature dependence of the RKKY interaction may change our interpretation of other models.

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